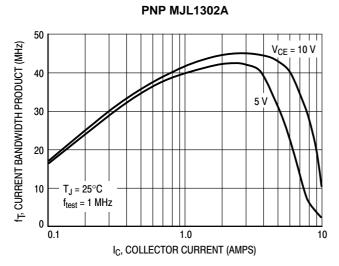
# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

| Characteristic   | Symbol                | Min                              | Max                           | Unit |
|--|-----------------------|----------------------------------|-------------------------------|------|
| OFF CHARACTERISTICS  |                       |                                  |                               |      |
| Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0)   | V <sub>CEO(sus)</sub> | 260                              | -                             | Vdc  |
| Collector Cutoff Current<br>(V <sub>CB</sub> = 260 Vdc, I <sub>E</sub> = 0)  | I <sub>CBO</sub>      | -                                | 50                            | μAdc |
| Emitter Cutoff Current $(V_{EB} = 5 \text{ Vdc}, I_C = 0)$   | I <sub>EBO</sub>      | -                                | 5                             | μAdc |
| SECOND BREAKDOWN   |                       |                                  |                               |      |
| Second Breakdown Collector with Base Forward Biased (V <sub>CE</sub> = 50 Vdc, t = 1 s (non–repetitive) (V <sub>CE</sub> = 100 Vdc, t = 1 s (non–repetitive)   | I <sub>S/b</sub>      | 4<br>1                           |                               | Adc  |
| ON CHARACTERISTICS   |                       |                                  |                               |      |
| DC Current Gain $ \begin{aligned} &(I_C = 500 \text{ mAdc, } V_{CE} = 5 \text{ Vdc}) \\ &(I_C = 1 \text{ Adc, } V_{CE} = 5 \text{ Vdc}) \\ &(I_C = 3 \text{ Adc, } V_{CE} = 5 \text{ Vdc}) \\ &(I_C = 5 \text{ Adc, } V_{CE} = 5 \text{ Vdc}) \\ &(I_C = 8 \text{ Adc, } V_{CE} = 5 \text{ Vdc}) \end{aligned} $ | h <sub>FE</sub>       | 75<br>75<br>75<br>75<br>75<br>45 | 150<br>150<br>150<br>150<br>- |      |
| Collector–Emitter Saturation Voltage (I <sub>C</sub> = 10 Adc, I <sub>B</sub> = 1 Adc)   | V <sub>CE(sat)</sub>  | -                                | 3                             | Vdc  |
| DYNAMIC CHARACTERISTICS  | •                     |                                  |                               |      |
| Current–Gain – Bandwidth Product $(I_C = 1 \text{ Adc}, V_{CE} = 5 \text{ Vdc}, f_{test} = 1 \text{ MHz})$   | f⊤                    | 30                               | -                             | MHz  |
| Output Capacitance<br>( $V_{CB} = 10 \text{ Vdc}, I_E = 0, f_{test} = 1 \text{ MHz}$ )   | C <sub>ob</sub>       | -                                | 600                           | pF   |

### **TYPICAL CHARACTERISTICS**



**NPN MJL3281A** 

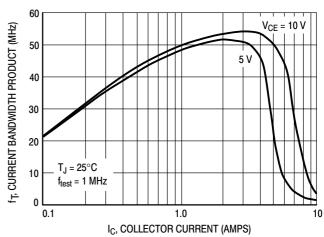
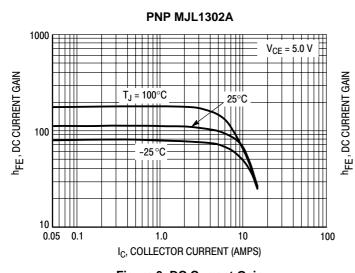


Figure 1. Typical Current Gain **Bandwidth Product** 

Figure 2. Typical Current Gain **Bandwidth Product** 



NPN MJL3281A

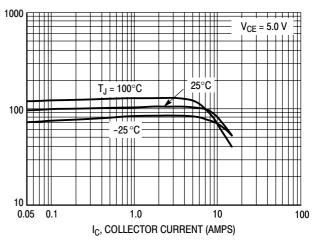
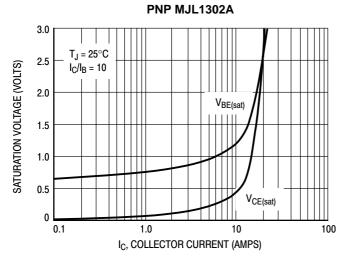


Figure 3. DC Current Gain

Figure 4. DC Current Gain



NPN MJL3281A

 $V_{\text{BE(sat)}}$ 

V<sub>CE(sat)</sub>

100

IC, COLLECTOR CURRENT (AMPS) Figure 6. Typical Saturation Voltages



2.5

2.0

1.5

0.5

0

0.1

SATURATION VOLTAGE (VOLTS)

 $T_J = 25^{\circ}C$ 

 $I_{C}/I_{B}=10$ 

### TYPICAL CHARACTERISTICS

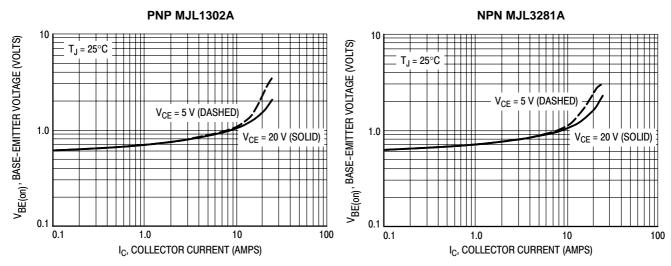


Figure 7. Typical Base-Emitter Voltage

Figure 8. Typical Base-Emitter Voltage

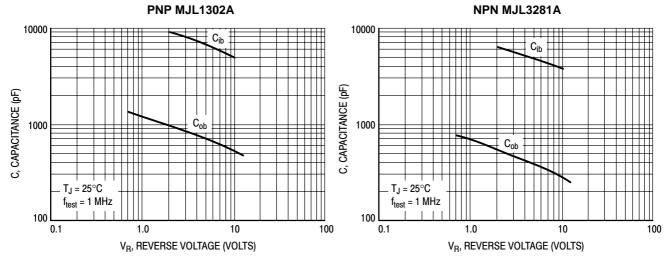


Figure 9. MJL1302A Typical Capacitance

Figure 10. MJL3281A Typical Capacitance

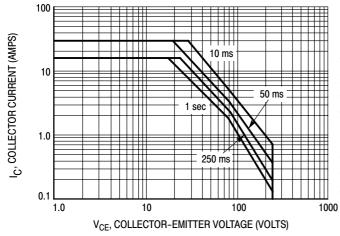


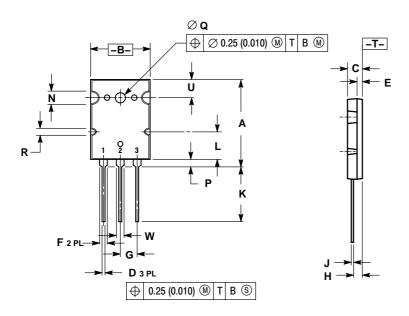
Figure 11. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 11 is based on  $T_{J(pk)} = 150^{\circ}\text{C}$ ;  $T_{C}$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

### PACKAGE DIMENSIONS

TO-3PBL (TO-264) CASE 340G-02 ISSUE J



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### NOTES

- DIMENSIONING AND TOLERANCING PER
   ANSLY 44 FM 4002
- ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.

|     | MILLIN   | IETERS | INCHES    |       |  |
|-----|----------|--------|-----------|-------|--|
| DIM | MIN      | MAX    | MIN       | MAX   |  |
| Α   | 28.0     | 29.0   | 1.102     | 1.142 |  |
| В   | 19.3     | 20.3   | 0.760     | 0.800 |  |
| С   | 4.7      | 5.3    | 0.185     | 0.209 |  |
| D   | 0.93     | 1.48   | 0.037     | 0.058 |  |
| E   | 1.9      | 2.1    | 0.075     | 0.083 |  |
| F   | 2.2      | 2.4    | 0.087     | 0.102 |  |
| G   | 5.45 BSC |        | 0.215 BSC |       |  |
| Н   | 2.6      | 3.0    | 0.102     | 0.118 |  |
| J   | 0.43     | 0.78   | 0.017     | 0.031 |  |
| K   | 17.6     | 18.8   | 0.693     | 0.740 |  |
| L   | 11.2 REF |        | 0.411 REF |       |  |
| N   | 4.35 REF |        | 0.172 REF |       |  |
| Р   | 2.2      | 2.6    | 0.087     | 0.102 |  |
| Q   | 3.1      | 3.5    | 0.122     | 0.137 |  |
| R   | 2.25 REF |        | 0.089 REF |       |  |
| U   | 6.3 REF  |        | 0.248 REF |       |  |
| w   | 2.8      | 3.2    | 0.110     | 0.125 |  |

STYLE 2:

PIN 1. BASE

2. COLLECTOR

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